19-2735; Rev 1; 3/04

EVALUATION KIT AVAILABLE ORing MOSFET Controllers with Fastest Fault Isolation for Redundant Power Supplies

General Description

Critical loads often employ parallel-connected power supplies with redundancy in order to enhance system reliability. The MAX8535/MAX8536/MAX8585 are highly integrated but inexpensive MOSFET controllers that provide isolation and redundant power capability in high-reliability systems. The MAX8535/MAX8585 are used in 12V systems, and have an internal charge pump to drive the gates of the n-channel pass elements to V_{CC} + 10V. The MAX8536 is used in 3.3V and 5V systems, with a charge pump output of V_{CC} + 5V.

During startup, the MAX8535/MAX8536/MAX8585 monitor the voltage drop across external MOSFETs. Once V_{CC} approaches or exceeds the bus voltage, the MOSFETs are turned on. The MAX8535/MAX8536/MAX8585 feature a dual-purpose TIMER input. A single external resistor from TIMER to ground sets the turn-on speed of the external MOSFETs. Optionally, the TIMER input can be used as a logic-enable pin. Once the device is turned on, the MAX8535/MAX8536/MAX8585 monitor the load, protecting against overvoltage, undervoltage, and reverse-current conditions.

Overvoltage and undervoltage fault thresholds are adjustable and can be disabled. The current-limit trip points are set by the external MOSFETs' R_{DS}(ON), reducing component count. An open-drain logic-low fault output indicates if an overvoltage, undervoltage, or reverse-current fault occurs.

All devices come in a space-saving 8-pin μ MAX[®] package and are specified over the extended -40°C to +85°C temperature range.

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Applications

Silver Box Supplies for Servers

On-Board Redundant Power Supplies in Blade Servers

Network/Telecom Power Supplies

Rectifiers

Redundant Power Supplies in High-Availability Systems

Pin Configuration, Functional Diagrams, and Typical Application Circuits appear at end of data sheet.

_Features

- Simple, Integrated, and Inexpensive ORing MOSFET Controller
- ORing MOSFET Drive for 12V (MAX8535/MAX8585) and 3.3V or 5V (MAX8536) Bus
- Eliminates ORing Diode Power Dissipation and Reverse Leakage Current
- Provides N + 1 Redundant Supply Capability for Highly Reliable Systems
- ♦ Isolates Failed Supply from Output Bus in <1µs</p>
- Reverse-Current Flow Detection
- Programmable Soft-Start
- Logic-Enable Input
- Adjustable Overvoltage and Undervoltage Trip Points
- Fault-Indicator Output
- ♦ Space-Saving 8-Pin µMAX Package

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX8535EUA	-40°C to +85°C	8 µMAX
MAX8535AEUA	-40°C to +85°C	8 µMAX
MAX8536EUA	-40°C to +85°C	8 μΜΑΧ
MAX8585EUA	-40°C to +85°C	8 μΜΑΧ

_Typical Operating Circuit



Maxim Integrated Products 1

For pricing, delivery, and ordering information, please contact Maxim/Dallas Direct! at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

ABSOLUTE MAXIMUM RATINGS

GATE to GND (MAX8535/MAX8535A/MAX8585)...-0.3V to +28V V_{CC} to GND (MAX8535/MAX8535A/MAX8585)-0.3V to +18V CS, FAULT to GND

(MAX8535/MAX8535A/MAX8585)	0.3V to +15V
GATE to GND (MAX8536)	-0.3V to (V _{CC} + 6V)
V _{CC} , CS, FAULT to GND (MAX8536)	0.3V to +6V
OVP, UVP, TIMER to GND	0.3V to +6V

Continuous Power Dissipation ($T_A = +70^{\circ}C$)	
8-Pin µMAX (derate 4.5mW/°C above +70°C)	362mW
Operating Temperature Range	40°C to +85°C
Storage Temperature Range69	5°C to +150°C
Junction Temperature	+150°C
Lead Temperature (soldering, 10s)	+300°C

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

 $(V_{CC} = 12V (MAX8535/MAX8535A/MAX8585), V_{CC} = 5V (MAX8536), V_{CS} = V_{CC} - 0.1V, R_{TIMER} = 25k\Omega, UVP = 2V, OVP = 1V, C_{GATE} = 0.01\mu F, T_A = 0^{\circ}C to +85^{\circ}C, unless otherwise noted.)$

PARAMETER	SYMBOL	CONDITIONS		MIN	ТҮР	MAX	UNITS
V _{CC} SUPPLY							·
V _{CC} Supply Current		TIMER = 2.5V	V _{CC} = 14V (MAX8535/ MAX8535A/MAX8585)		2	4.5	mA
			V _{CC} = 6V (MAX8536)		2	3	
V _{CC} Shutdown Current		TIMER = 0V	V _{CC} = 14V (MAX8535/ MAX8535A/MAX8585)			4.5	mA
			V _{CC} = 6V (MAX8536)			3	
			MAX8535/MAX8535A/ MAX8585, charge pump on	8		14	
V _{CC} Input Voltage		TIMER = 2.5V	MAX8536, charge pump on	3.0		5.5	V
			MAX8535/MAX8535A/ MAX8585, charge pump off			17	
CS Input Current		TIMER = 2.5V	CS = 14V (MAX8535/ MAX8535A/MAX8585)		100		μA
			CS = 5.5V (MAX8536)		50		
CS Isolation		CS = max opera	ating voltage, $V_{CC} = 0V$, $I(V_{CC})$		-0.05	-1	μA
V _{CC} Undervoltage Lockout	Vссок	MAX8535/MAX threshold	(8535A/MAX8585, rising	6	6.5	7	V
		MAX8536, risir	ng threshold	2.5	2.7	2.9	1
V _{CC} Overvoltage Internal		MAX8535/ MAX8535A/	Rising threshold	14	14.5	15	V
Threshold		MAX8585	Falling threshold	13.3	13.9	14.5	v
CHARGE-PUMP VOLTAGE			·				
		Measured from (MAX8536)	N VGATE to VCC, VCC = $3.3V$	5	5.5	6	
Gate Voltage	Vgate	V _{CC} = 5V (MAX8536)		5	5.5	6	- V
		$V_{CC} = 12V$ (MA	X8535/MAX8535A/MAX8585)	9	11	12	



ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = 12V \text{ (MAX8535/MAX8535A/MAX8585)}, V_{CC} = 5V \text{ (MAX8536)}, V_{CS} = V_{CC} - 0.1V, R_{TIMER} = 25k\Omega, UVP = 2V, OVP = 1V, C_{GATE} = 0.01\mu\text{F}, T_A = 0^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.})$

PARAMETER	SYMBOL		CONDITIONS	MIN	ТҮР	MAX	UNITS
		R _{TIMER} = 20k	Ω	1	187		
Charge-Pump Switching		R _{TIMER} = 125		1	450		1.0
Frequency		R _{TIMER} = open V _{TIMER} = 1.5V			500		kHz
					550		
TIMER	•			•			
TIMER Voltage				1.219	1.25	1.281	V
TIMER Maximum Source Current		V _{TIMER} = 1V		80	100	120	μA
TIMER High-Input Current		VTIMER = 1.5	/		10	20	μA
TIMER Maximum Frequency		MAX8535/MA	X8535A/MAX8585	1.5		3.4	
Select Voltage Input Range		MAX8536		1.5		V _{CC} - 0.6	V
TIMER Logic High	VIH	Charge pump	enabled	1.0			V
TIMER Logic Low	VIL	Charge pump	disabled			0.5	V
FAULT							
Fault Output Low Voltage		$I_{FAULT} = 0.5m$	۱A			0.8	V
Fault Sink Current		FAULT = 0.8	1	0.5			mA
		FAULT = 18V (I	VIAX8535 /MAX8535A/MAX8585)			5	<u>,</u>
Fault Leakage Current		FAULT = 6V (MAX8536)				5	μA
GATE							
Gate On Threshold		Measured from V _{CC} to CS		0.3	0.4	0.5	V
		Vgate =	I _{TIMER} = 0μΑ (ΜΑΧ8535/ ΜΑΧ8535Α/ΜΑΧ8585)	35	50	65	μA
Gate Drive Current		$V_{CC} = 12V$	I _{TIMER} = 50µA (MAX8535/ MAX8535A/MAX8585)	15	25	36	
		Vgate =	I _{TIMER} = 0μΑ (ΜΑΧ8536)	17	25	33	
		$V_{CC} = 5V$	$I_{\text{TIMER}} = 50 \mu \text{A} (\text{MAX8536})$	8	12	16	
Gate Shutdown Delay			nse to the start of gate voltage In TIMER to the start of gate		200	300	ns
		GATE = V _{CC}	+ 5V (MAX8535/MAX8536)	100	200	300	1
Gate Discharge Current		GATE = V _{CC}	+ 5V (MAX8535A/MAX8585)	200	300	400	mA
Gate Fall Time		Gate voltage fall from fault to $V_{GATE} = V_{CC}$, $C_{GATE} = 0.01 \mu F$ (200ns + CV/I = 700ns, typ) (MAX8535/MAX8536)			0.7		μs
		MAX8535A/MAX8585		1	0.55		
CURRENT SENSE							
Reverse-Current Threshold		Measured from (MAX8535/MA	m CS to V _{CC} AX8535A/MAX8536)	20	30	40	mV
		MAX8585	· · · · · ·		0	+3	

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = 12V \text{ (MAX8535/MAX8535A/MAX8585)}, V_{CC} = 5V \text{ (MAX8536)}, V_{CS} = V_{CC} - 0.1V, R_{TIMER} = 25k\Omega, UVP = 2V, OVP = 1V, C_{GATE} = 0.01\mu\text{F}, T_A = 0^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.})$

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
Startup Reverse-Current Blank Time		TIMER = open (MAX8535/MAX8535A/ MAX8536)		524		ms	
line		MAX8585		32			
Forward-Current Threshold		Measured from V _{CC} to CS	5	10	15	mV	
OVERVOLTAGE PROTECTION							
		OVP rising	1.219	1.25	1.281		
OVP Fault Threshold	Vovp	OVP falling		1.2		V	
OVP Bias Current					0.2	μA	
UNDERVOLTAGE PROTECTION	N						
UVP Fault Voltage		UVP rising threshold	1.219	1.25	1.281	N	
	Vuvp	UVP falling threshold	1.119	1.15	1.181	V	
UVP Bias Current			İ		0.4	μA	

ELECTRICAL CHARACTERISTICS

 $(V_{CC} = 12V (MAX8535/MAX8535A/MAX8585), V_{CC} = 5V (MAX8536), V_{CS} = V_{CC} - 0.1V, R_{TIMER} = 25k\Omega, UVP = 2V, OVP = 1V, C_{GATE} = 0.01\mu$ F, T_A = -40°C to +85°C, unless otherwise noted.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS		MIN	ТҮР	MAX	UNITS
V _{CC} SUPPLY							
V _{CC} Supply Current		TIMER = 2.5V	V _{CC} = 14V (MAX8535/ MAX8535A/MAX8585)			4.5	mA
			V _{CC} = 6V (MAX8536)			3	
V _{CC} Shutdown Current		TIMER = 0V	V _{CC} = 14V (MAX8535/ MAX8535A/MAX8585)			4.5	mA
			V _{CC} = 6V (MAX8536)			3	1
			MAX8535/MAX8535A/ MAX8585, charge pump on	8		14	V
V _{CC} Input Voltage		TIMER = 2.5V	MAX8536, charge pump on	3.0		5.5	
			MAX8535/MAX8535A/ MAX8585, charge pump off			17	
CS Isolation		CS = max opera	ating voltage, $V_{CC} = 0V$, $I(V_{CC})$			-1	μA
V _{CC} Undervoltage Lockout	Vссок	(MAX8535/MA threshold	(MAX8535/MAX8535A/MAX8585) rising threshold			7.0	V
		(MAX8536) risi	ng threshold	2.5		2.9	
V _{CC} Overvoltage Internal		(MAX8535/ MAX8535A/	Rising threshold	14		15	V
Threshold		MAX8585)	Falling threshold	13.3		14.5	v

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = 12V (MAX8535/MAX8535A/MAX8585), V_{CC} = 5V (MAX8536), V_{CS} = V_{CC} - 0.1V, R_{TIMER} = 25k\Omega, UVP = 2V, OVP = 1V, C_{GATE} = 0.01\mu$ F, **T_A = -40°C to +85°C**, unless otherwise noted.) (Note 1)

PARAMETER	SYMBOL		CONDITIONS	MIN	ТҮР	MAX	UNITS
CHARGE-PUMP VOLTAGE	1			1			
		Measured from (MAX8536)	n VGATE to VCC, VCC = $3.3V$	5		6	
Gate Voltage	Vgate	$V_{CC} = 5V$ (MA	X8536)	5		6	V
		$V_{CC} = 12V (MA)$	X8535/MAX8535A/MAX8585)	9		12	
TIMER							
TIMER Voltage				1.200		1.281	V
TIMER Maximum Source Current		$V_{\text{TIMER}} = 1.0V$	1	80		120	μΑ
TIMER High-Input Current		$V_{TIMER} = 1.5V$	1			20	μΑ
TIMER Maximum Frequency		MAX8535/MA	MAX8535/MAX8535A/MAX8585			3.4	V
Select Voltage Input Range		MAX8536	MAX8536		١	/ _{CC} - 0.6	V
TIMER Logic High	VIH	Charge pump	enabled	1.1			V
TIMER Logic Low	VIL	Charge pump	disabled			0.5	V
FAULT							
Fault Output Low Voltage		$I_{FAULT} = 0.5 mA$				0.8	V
Fault Sink Current		$\overline{FAULT} = 0.8V$		0.5			mA
Fault Leakage Current		FAULT = 18V (MAX8535/ MAX8535A/MAX8585) FAULT = 6V (MAX8536)				5	μA
5						5	·
GATE		,	·				
Gate On Threshold		Measured fror	n V _{CC} to CS	0.3		0.5	V
		Vgate =	I _{TIMER} = 0μΑ (ΜΑΧ8535/ ΜΑΧ8535Α/ΜΑΧ8585)	35		65	
Gate-Drive Current		V _{CC} = 12V	I _{TIMER} = 50µА (МАХ8535/ МАХ8535А/МАХ8585)	15		36	μA
		VGATE =	I _{TIMER} = 0μΑ (ΜΑΧ8536)	17		33	
		$V_{CC} = 5V$	I _{TIMER} = 50μΑ (ΜΑΧ8536)	8		16	
Gate Shutdown Delay		From fault sense to the start of gate voltage falling, or from TIMER to the start of gate voltage falling				300	ns
		GATE = VCC -	+ 5V (MAX8535/MAX8536)	100		300	
Gate Discharge Current		MAX8535A/MAX8585		200		400	mA
CURRENT SENSE		1					
Reverse-Current Threshold		Measured from (MAX8535/MA	n CS to V _{CC} \X8535A/MAX8586)	20		40	mV
		MAX8585		-5		+5	
Forward-Current Threshold		Measured from	m V _{CC} to CS	5		15	mV

ELECTRICAL CHARACTERISTICS (continued)

 $(V_{CC} = 12V \text{ (MAX8535/MAX8535A/MAX8585), } V_{CC} = 5V \text{ (MAX8536), } V_{CS} = V_{CC} - 0.1V, \\ R_{TIMER} = 25k\Omega, \\ UVP = 2V, \\ OVP = 1V, \\ C_{GATE} = 0.01\mu\text{F}, \\ \textbf{T}_{\textbf{A}} = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \\ \text{unless otherwise noted.)} \text{ (Note 1)}$

PARAMETER	SYMBOL	CONDITIONS	MIN	ТҮР	MAX	UNITS
OVERVOLTAGE PROTECTION						
OVP Fault Threshold	Vovp	OVP rising	1.20		1.281	V
OVP Bias Current					0.2	μΑ
UNDERVOLTAGE PROTECTION						
	Man	UVP rising threshold	1.200		1.281	V
UVP Fault Voltage	Vuvp	UVP falling threshold	1.10		1.19	
UVP Bias Current					0.4	μA

Note 1: Specifications to -40°C are guaranteed by design and not production tested.

State Diagram



MAX8535 Typical Operating Characteristics

 $(V_{CC} = 12V, R_{TIMER} = 25k\Omega, UVP = 2V, OVP = 1V, C_{GATE} = 0.01\mu$ F, BUS = 100 μ F, T_A = +25°C, unless otherwise specified.)













UVP AND OVP LEAKAGE CURRENT vs. TEMPERATURE





4ms/div



Vcs



_MAX8535 Typical Operating Characteristics (continued)

10V/div

 $(V_{CC} = 12V, R_{TIMER} = 25k\Omega, UVP = 2V, OVP = 1V, C_{GATE} = 0.01\mu$ F, BUS = 100 μ F, T_A = +25°C, unless otherwise specified.)



1µs/div

MAX8536 Typical Operating Characteristics

 $(V_{CC} = 12V, R_{TIMER} = 25k\Omega, UVP = 2V, OVP = 1V, C_{GATE} = 0.01\mu$ F, BUS = 100 μ F, T_A = +25°C, unless otherwise specified.)









4ms/div



POWER-UP WAVEFORM (V_{BUS} = 5V)



_MAX8536 Typical Operating Characteristics (continued)

 $(V_{CC} = 12V, R_{TIMER} = 25k\Omega, UVP = 2V, OVP = 1V, C_{GATE} = 0.01\mu$ F, BUS = 100 μ F, T_A = +25°C, unless otherwise specified.)







VTIMER

2V/div

IMOSFET

1A/div

V_{GATE} 10V/div

 V_{CS}

5V/div

1.25V

VUVP

2V/div

V_{FAULT} 5V/div

VGATE

V_{CS} 1V/div

_Pin Description

PIN	NAME	FUNCTION
1	GATE	Gate Drive Output. Bypass GATE with a 0.01µF capacitor to ground.
2	GND	Ground
3	V _{CC}	Power-Supply Input. Bypass V_{CC} with a 0.1µF capacitor to ground.
4	UVP	Undervoltage Input. Connect a resistor-divider from the V_{CC} to GND with the center point connected to UVP. Leave high impedance if not used. UVP fault threshold must be set above V_{CCOK} threshold.
5	TIMER	Timer Input. Connect a resistor from TIMER to ground to select the charge-pump operating frequency. The charge-pump frequency is proportional to the TIMER output current. TIMER can source up to 100µA. If pulled low (<0.5V), the gate drive is disabled. If pulled high (above 1.25V), the charge pump operates at 550kHz.
6	OVP	Overvoltage Input. Connect a resistor-divider from the CS to GND with the center point connected to OVP. Connect to GND if not used.
7	FAULT	Open-Drain Fault Output. FAULT is low during a fault, high impedance during normal operation. Connect a pullup resistor of $50k\Omega$ or higher value to a voltage rail.
8	CS	Current-Sensing Input. Connect CS to the positive side of the system bus. Bypass with 1nF capacitor to GND.

_Detailed Description

Critical loads often employ parallel-connected power supplies with redundancy to enhance system reliability. The MAX8535/MAX8536/MAX8585 are highly integrated but inexpensive MOSFET controllers that provide isolation and redundant power capability in high-reliability systems. The MAX8535/MAX8585 is used in 12V systems and has an internal charge pump to drive the gates of the n-channel pass elements to V_{CC} + 10V. The MAX8536 is used in 3.3V and 5V systems, with a charge pump output of V_{CC} + 5V.

During startup, the MAX8535/MAX8536/MAX8585 monitor the voltage drop across external MOSFETs. Once V_{CC} approaches or exceeds the bus voltage, the MOSFETs are turned on. The MAX8535/MAX8536/MAX8585 feature a dual-purpose TIMER input. A single external resistor from TIMER to ground sets the turn-on speed of the external MOSFETs. Optionally, the TIMER input can be used as a logic-enable pin. Once the device is turned on, the MAX8535/MAX8536/MAX8585 monitor the load, protecting against overvoltage, undervoltage, and reverse-current conditions.

Overvoltage and undervoltage fault thresholds are adjustable and can be disabled. The current-limit trip points are set by the external MOSFETs' RDS(ON), reducing component count. An open-drain logic-low fault output indicates if an overvoltage, undervoltage, or reverse-current fault occurs.

Vcc

V_{CC} is the power-supply input for the MAX8535/ MAX8536/MAX8585 and the input to the internal charge pump that drives the gate of the external MOSFETs. The MAX8535/MAX8536/MAX8585 monitor V_{CC} at all times. V_{CC} connects directly to the power supply (Silver Box or DC-DC power modules). During startup, the device turns on when V_{CC} rises above the undervoltage threshold V_{CCOK}. After V_{CC} exceeds V_{CCOK} and V_{CC} is greater than (CS - 0.4V), the charge pump turns on, driving GATE high and turning on the external MOSFETs.

TIMER

The MAX8535/MAX8536/MAX8585 provide a programmable-frequency charge pump and shutdown function through TIMER. Slowing down the charge-pump frequency allows a user to program soft-start. Connecting a resistor from TIMER to GND sets the charge-pump frequency from 100kHz to 500kHz. Connecting TIMER to a logic high sets charge-pump operation to a maximum frequency of 550kHz. Pulling TIMER to GND shuts down the charge pump and turns off the external MOSFET. Reducing the charge-pump frequency increases the IREVERSE startup blank time (see the *Reverse-Current Fault* section).

GATE

GATE is the output of the internal charge pump that drives the external MOSFETS. During startup, the GATE voltage ramps up according to the charge-pump frequency. At 250kHz, the GATE drive current for the MAX8535/MAX8585 is 25µA and the GATE drive current



for the MAX8536 is 12 μ A. Increasing the charge-pump frequency increases the GATE drive current. Adding a resistor from GATE to the gate of the external MOSFETs further increases turn-on and turn-off times.

CS

The voltage drop across the external MOSFETs is measured between the V_{CC} and CS inputs. CS connects to the positive side of the system bus. The voltage drop across the CS and V_{CC} determines operation modes. IFORWARD is defined as V_{CC} - CS > 0.01V. IREVERSE is defined as CS - V_{CC} > 0.03V in all except the MAX8585. In the MAX8585, IREVERSE = 0V.

FAULT Conditions

The MAX8535/MAX8536/MAX8585 contain a versatile FAULT output that signals overvoltage, undervoltage, or reverse-current conditions. During a FAULT condition, the charge pump shuts down and the GATE discharges to ground.

Undervoltage Fault

The MAX8535/MAX8536/MAX8585 turn off the external MOSFET if the input voltage falls below the UVP threshold. If UVP is left unconnected, the undervoltage input is disabled. Set the undervoltage threshold to any value above V_{CCOK} . When the input voltage rises above the UVP threshold, FAULT clears and the MOSFET turns back on.

Overvoltage Fault

The MAX8535/MAX8536/MAX8585 contain an adjustable OVP feature. A resistor-divider from the CS system bus to the OVP input pin sets the overvoltage threshold. When the OVP level is exceeded and the part is in the IFORWARD condition (defined as $V_{CC} > CS + 0.01V$), the MAX8535/MAX8536/MAX8585 turn off the external MOSFET and a fault is latched. If there is no IFORWARD condition, an OVP detection has no

effect. In this way, only the input supply, which is causing the overvoltage condition, is turned off in a redundant power system application. An overvoltage fault is a latching fault condition, and requires V_{CC} or TIMER to be cycled to reset the part.

Reverse-Current Fault

The MAX8535/MAX8536 contain a reverse-current protection feature. If, after the 500ms (typ) startup blank time, an I_{REVERSE} condition is detected, the MAX8535/ MAX8536 turn off the external MOSFET and a fault is latched. A reverse-current fault forces the MAX8535/ MAX8536 to latch off. Cycle V_{CC} or TIMER to exit a latched fault condition. Startup blanking time allows the incoming power supply to connect to the system bus at V_{BUS} - 0.4V. Reducing charge-pump frequency increases the startup blanking time. The MAX8585 does not latch this fault.

Applications Information

Selecting the Timer Resistor

To set the frequency of the internal charge-pump operation, connect a resistor from TIMER to GND. Determine the frequency by using the equation:

Frequency =
$$5 \times \left(100 \mu A - \frac{1.25 V}{R_{TIMER}} \right) kHz/\mu A$$

Pull TIMER above 1.5V for maximum charge-pump frequency. Pull TIMER below 0.5V to disable the charge pump. Leave TIMER unconnected for a 500kHz charge-pump frequency.

Selecting the Gate Capacitor and Gate Resistor

The charge pump uses an internal monolithic transfer capacitor to charge the external MOSFET gates.

FAULT MODE	PIN CONDITIONS	GATE PIN	FAULT PIN	LATCHING
V _{CC} UVLO	V _{CC} < V _{CCOK}	Low	High impedance	No
UVP pin undervoltage protection	UVP < 1.25V	Low	Low	No
OVP pin overvoltage protection	OVP > 1.25V V _{CC} > CS + 0.01V	Low	Low	Yes
Reverse-current protection (MAX8535/MAX8536)	V _{CC} < CS - 0.03V Gate ON for t > 0.5s	Low	Low	Yes
Reverse-current protection (MAX8585)	V _{CC} < CS Gate ON for t > 0.032s	Low	Low	No
V _{CC} internal (MAX8535/MAX8585) overvoltage protection	V _{CC} > 14.5V	Low	Low	No

Table 1. MAX8535/MAX8536/MAX8585 Fault Modes

Normally, the external MOSFET's gate capacitance is sufficient to serve as a reservoir capacitor. If the MOSFETs are located at a significant distance from the MAX8535/MAX8536/MAX8585, place a local bypass capacitor (0.01 μ F, typ) across GATE and GND. For slower turn-on times, add a small capacitor between GATE and GND and a series resistor between GATE and the gate of the MOSFETs.

Set the UVP Fault Threshold

To set the undervoltage lockout threshold, use a resistordivider connected between V_{CC} and GND, with the center node of the divider connected to UVP. For example, use a $10k\Omega$ resistor (R4 in Figure 4) from UVP to GND and calculate the other resistor (R3) using:

$$R3 = R4 \left(\frac{V_{UVLO}}{V_{UVP}} - 1 \right)$$

where V_{UVLO} is the desired undervoltage lockout voltage and V_{UVP} is the UVP reference threshold specified in the *Electrical Characteristics* (1.25V, typ). To defeat the UVP, leave UVP unconnected.

Set the OVP Fault Threshold

To set the OVP threshold, use a resistor-divider connected between CS and GND, with the center node of the divider connected to OVP. For example, use a $10k\Omega$ resistor (R6 in Figure 4) from OVP to GND and calculate the other resistor, R5, using:

$$R5 = R6 \left(\frac{V_{OVLO}}{V_{OVP}} - 1 \right)$$

where V_{OVLO} is the desired overvoltage lockout voltage and V_{OVP} is the OVP reference threshold specified in the *Electrical Characteristics* (1.25V, typ). To defeat the OVP, connect the OVP input to GND.

MOSFET Selection

The MAX8535/MAX8536/MAX8585 drive n-channel MOSFETs. The most important feature of the MOSFETs is R_{DS(ON)}. As load current flows through the external MOSFET, a voltage (V_{DS}) is generated from drain-to-source due to the MOSFET's on-resistance, R_{DS(ON)}. The MAX8535/MAX8536/MAX8585 monitor V_{DS} of the

MOSFETs at all times. The MAX8535/MAX8536/ MAX8585 determine the state of the monitored power supply by measuring the voltage drop across the external MOSFETs. With two external MOSFETs, the equation becomes:

VDSTOTAL = RDS(ON)1 X ILOAD + RDS(ON)2 X ILOAD

Selecting a MOSFET with a low R_{DS(ON)} allows more current to flow through the MOSFETs before the MAX8535/MAX8536/MAX8585 detect reverse-current (I_{REVERSE}) and forward-current (I_{FORWARD}) conditions.

Using a Single MOSFET

Single MOSFETs can be used if the OVP function is not needed. Connect the source of the MOSFET to V_{CC} and the drain of the MOSFET to CS.

Layout Guidelines

Keep all traces as short as possible and maximize the high-current trace width to reduce the effect of undesirable parasitic inductance. The MOSFET generates a fair amount of heat because of the high currents involved. In order to dissipate the heat generated by the MOSFET, make the power traces very wide with a large amount of copper area, and place the MAX8535/ MAX8536/MAX8585 as close as possible to the drain of the external MOSFET. A more efficient way to achieve good power dissipation on a surface-mount package is to lay out two copper pads directly under the MOSFET package on both sides of the board. Connect the two pads to the ground plane through vias and use enlarged copper mounting pads on the topside of the board. Use a ground plane to minimize impedance and inductance. Refer to the MAX8535 Evaluation Kit data sheet for an example of a PC board layout.

In addition to the usual high-power considerations, bypassing prevent false faults by:

- 1) Bypass V_{CC} with a 0.1µF capacitor to ground and bypassing CS with a 1nF capacitor to ground.
- 2) Making the traces connecting UVP and OVP as short as possible.
- 3) Kelvin connecting V_{CC} and CS to the external MOSFET.

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_Functional Diagrams



Figure 1. MAX8535/MAX8585 Functional Diagram



Figure 2. MAX8536 Functional Diagram





Typical Application Circuits

Figure 3. Typical Application Circuit for 12V/20A Output with OVP and UVP



Figure 4. Typical Application Circuit for 3.3V or 5V/20A Output with OVP and UVP



Figure 5. Typical Application Circuit for 12V/20A Output without OVP and UVP



Pin Configuration



_Chip Information

TRANSISTOR COUNT: 3011 PROCESS: BICMOS

Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to **www.maxim-ic.com/packages**.)



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MAX8535/MAX8536/MAX8585

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